

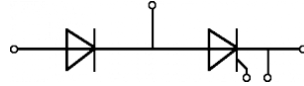
Thyristor/Diode module

PSKH 252M

$I_{T(RMS)} = 2x 390 A$
 $I_{T(AV)} = 2x 250 A$
 $V_{RRM} = 800-1800 V$

Preliminary Data Sheet

V_{RSM} V	V_{RRM} V	Type
900	800	PSKH 252M/08
1100	1000	PSKH 252M/10
1300	1200	PSKH 252M/12
1500	1400	PSKH 252M/14
1700	1600	PSKH 252M/16
1900	1800	PSKH 252M/18



Symbol	Test Conditions	Maximum Ratings
$I_{TR(MS)}$	$T_{VJ} = 125^{\circ}C$	half sine 390 A
$I_{TA(V)}$	$T_C = 85^{\circ}C$	250 A
I_{TSM}	$T_{VJ} = 125^{\circ}C$ t = 10 ms	half sine 9000 A
$\int i^2 dt$	$T_{VJ} = 125^{\circ}C$ t = 10 ms	half sine 405 A ² s*10 ³
$(di/dt)_{cr}$	$T_{VJ} = 125^{\circ}C$ t _r ≤ 0,5μs	gate source 1,5A 200 A/μs
$(dv/dt)_{cr}$	$T_{VJ} = 125^{\circ}C$ V _{DM} =2/3V _{DRM}	1000 V/μs
T_{VJ}		-40 ... + 125 °C
T_{VJM}		125 °C
T_{stg}		-40 ... + 125 °C
V_{ISOL}	50 HZ, RMS t = 1 min I _{ISOL} ≤ 1 mA	min. 3000 V ~
M_d	Terminal connection torque (M8) Mounting torque (M6)	12,0 Nm 6,0 Nm
Weight	typ.	820 g

Features

- Isolated mounting base 3000V~
- Pressure contact technology with increased power cycling capability

Applications

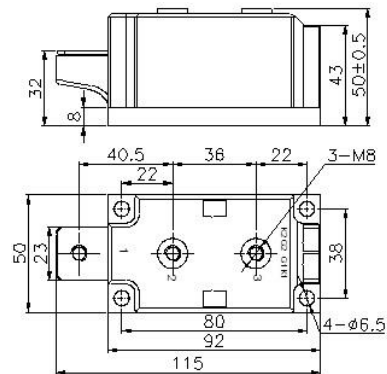
- AC/DC Motor drives
- Various rectifiers
- DC supply for PWM inverter

Advantages

- Easy to mount
- Space and weight savings
- Improved temperature and power cycling capability

Package, style and outline

Dimensions in mm (1mm = 0.0394")



Symbol	Test Conditions	Characteristic Value
$I_{RRM}; I_{DRM}$	V _R = V _{RRM} T _{VJ} = 125°C V _D = V _{DRM}	≤ 25 mA
V_{TM}	I _{TM} = 750 A T _{VJ} = 25°C	≤ 1,57 V
V_{TO}	For power-loss calculations only	0,80 V
r_t	T _{VJ} = 125°C	0,85 mΩ
I_{GT}		30-180 mA
V_{GT}	V _A = 12 V T _{VJ} = 25°C I _A = 1 A	1,0-2,5 V
I_H		20-180 mA
V_{GD}	V _{DM} =2/3V _{DRM} T _{VJ} = 125°C	0,2 V
$R_{th(j-c)}$	Per chip; Single side cooled	0,12 °C/W